SKM 600GA126D

SEMITRANS® 4

Trench IGBT Modules

SKM 600GA126D

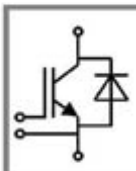
Preliminary Data

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications

- AC inverter drives
- UPS
- Electronic welders



GA

Absolute Maximum Ratings		T_{case} = 25°C, unless otherwise specified		
Symbol	**Conditions**		**Values**	**Units**
IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	T_j = 150 °C	T_c = 25 °C	660	A
		T_c = 80 °C	460	A
I_{CRM}	I_{CRM}=2xI_{Cnom}		800	A
V_{GES}			± 20	V
t_{psc}	V_{CC} = 600 V; V_{GE} ≤ 20 V; V_{CES} < 1200 V	T_j = 125 °C	10	µs
Inverse Diode				
I_F	T_j = 150 °C	T_c = 25 °C	490	A
		T_c = 80 °C	340	A
I_{FRM}	I_{FRM}=2xI_{Fnom}		800	A
I_{FSM}	t_p = 10 ms; sin.	T_j = 150 °C	2900	A
Module				
$I_{t(RMS)}$			500	A
T_{vj}			-40 ...+ 150	°C
T_{stg}			-40 ... + 125	°C
V_{isol}	AC, 1 min.		4000	V

Characteristics		T_{case} = 25°C, unless otherwise specified				
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
IGBT						
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 16 mA		5	5,8	6,5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = V_{CES}	T_j = 25 °C		0,2	0,6	mA
		T_j = 125 °C				mA
V_{CE0}		T_j = 25 °C		1	1,2	V
		T_j = 125 °C		0,9	1,1	V
r_{CE}	V_{GE} = 15 V	T_j = 25°C		1,8	2,4	mΩ
		T_j = 125°C		2,8	3,4	mΩ
$V_{CE(sat)}$	I_{Cnom} = 400 A, V_{GE} = 15 V	T_j = 25°C$_{chiplev.}$		1,7	2,15	V
		T_j = 125°C$_{chiplev.}$		2	2,45	V
C_{ies}				29		nF
C_{oes}	V_{CE} = 25, V_{GE} = 0 V	f = 1 MHz		1,5		nF
C_{res}				1,3		nF
Q_G	V_{GE} = -8V - +20V			3600		nC
R_{Gint}	T_j = °C			1,88		Ω
$t_{d(on)}$	R_{Gon} = 2 Ω	V_{CC} = 600V		330		ns
t_r		I_{Cnom} = 400A		65		ns
E_{on}		T_j = 125 °C		39		mJ
$t_{d(off)}$	R_{Goff} = 2 Ω	V_{GE} = ± 15V		630		ns
t_f				130		ns
E_{off}				64		mJ
$R_{th(j-c)}$	per IGBT				0,055	K/W

SKM 600GA126D

SEMITRANS® 4

Trench IGBT Modules

SKM 600GA126D

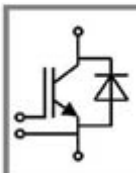
Preliminary Data

Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to 6 x I_C

Typical Applications

- AC inverter drives
- UPS
- Electronic welders



GA

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Units**
Inverse diode						
$V_F = V_{EC}$	I_{From} = 400 A; V_{GE} = 0 V	T_j = 25 °C $_{chiplev.}$		1,6	1,8	V
		T_j = 125 °C $_{chiplev.}$		1,6	1,8	V
V_{F0}		T_j = 25 °C		1	1,1	V
		T_j = 125 °C		0,8	0,9	V
r_F		T_j = 25 °C		1,5	1,8	mΩ
		T_j = 125 °C		2	2,3	mΩ
I_{RRM}	I_{From} = 400 A	T_j = 125 °C		350		A
Q_{rr}	di/dt = 5800 A/µs			87		µC
E_{rr}	V_{GE} = -15 V; V_{CC} = 600 V					mJ
$R_{th(j-c)D}$	per diode				0,125	K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip	T_{case} = 25 °C		0,18		mΩ
		T_{case} = 125 °C		0,22		mΩ
$R_{th(c-s)}$	per module				0,038	K/W
M_s	to heat sink M6		3		5	Nm
M_t	to terminals M6 (M4)		2,5 (1,1)		5 (2)	Nm
w					330	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

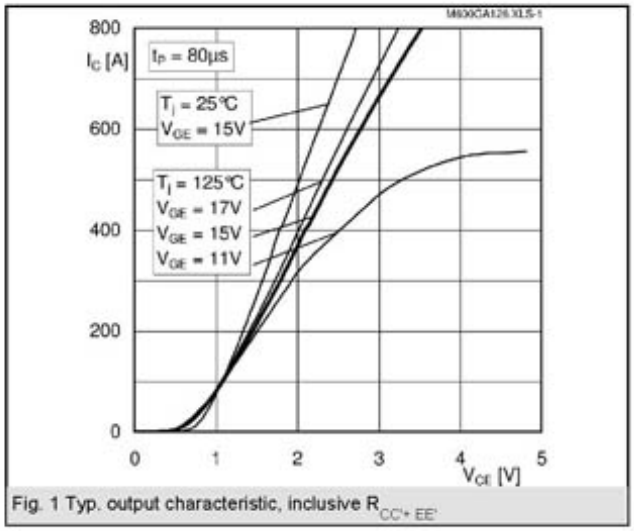


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

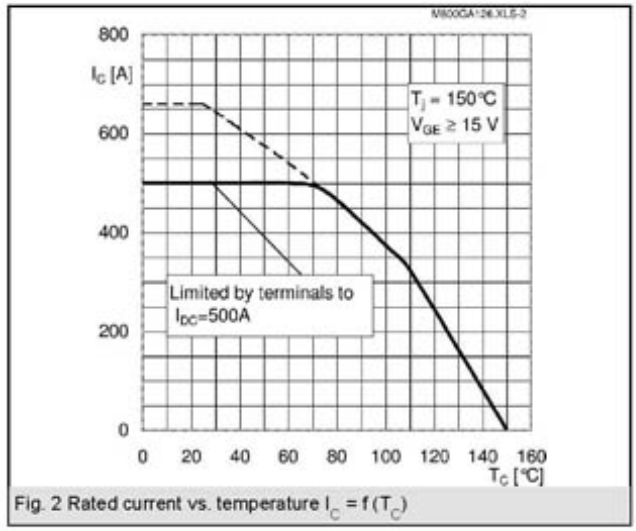


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

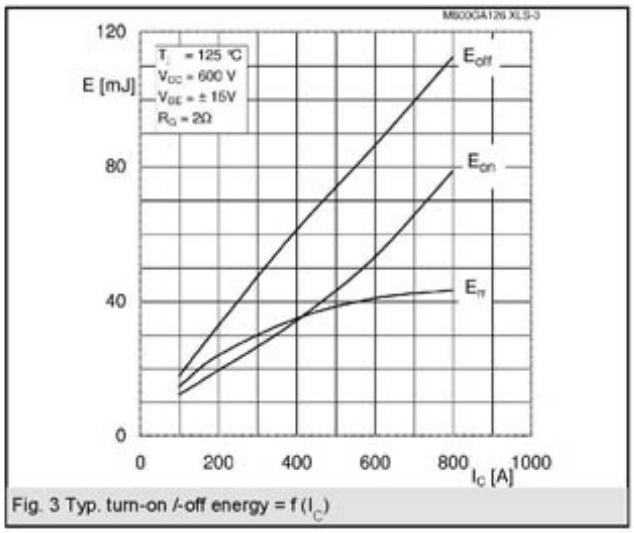


Fig. 3 Typ. turn-on /-off energy = f (I_C)

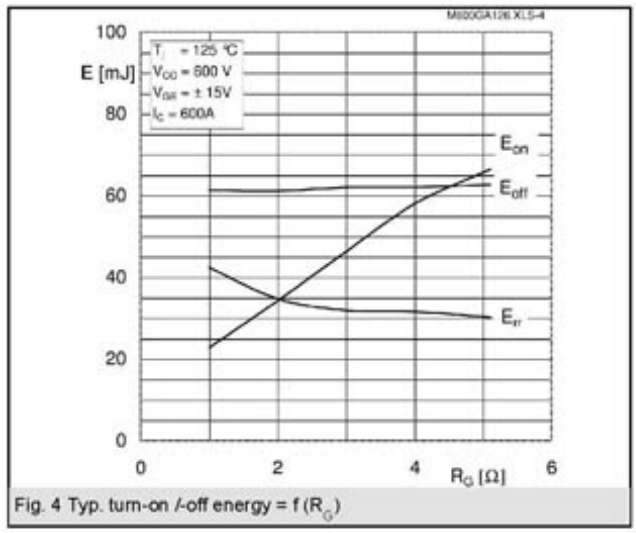


Fig. 4 Typ. turn-on /-off energy = f (R_G)

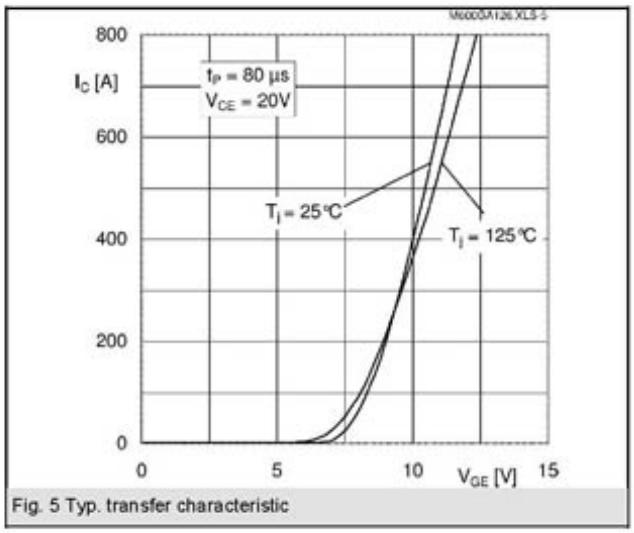


Fig. 5 Typ. transfer characteristic

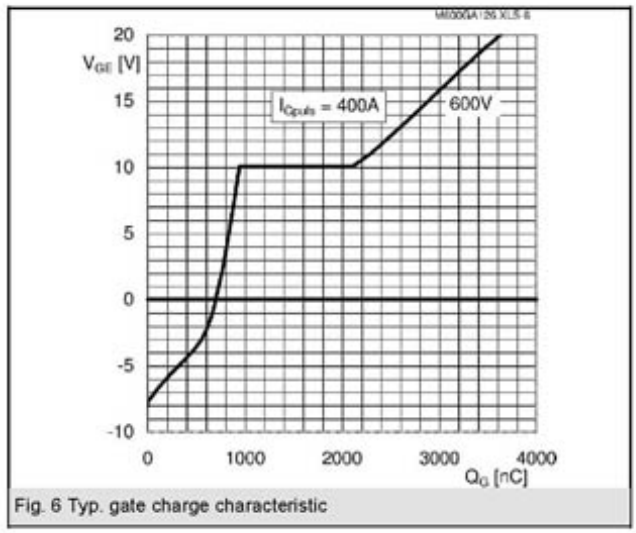


Fig. 6 Typ. gate charge characteristic

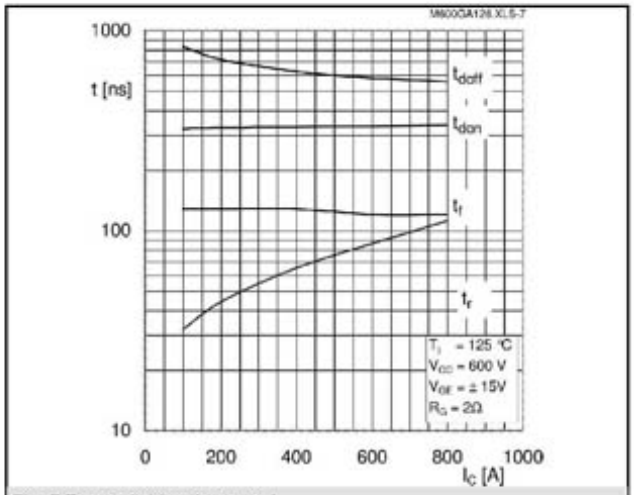


Fig. 7 Typ. switching times vs. I_C

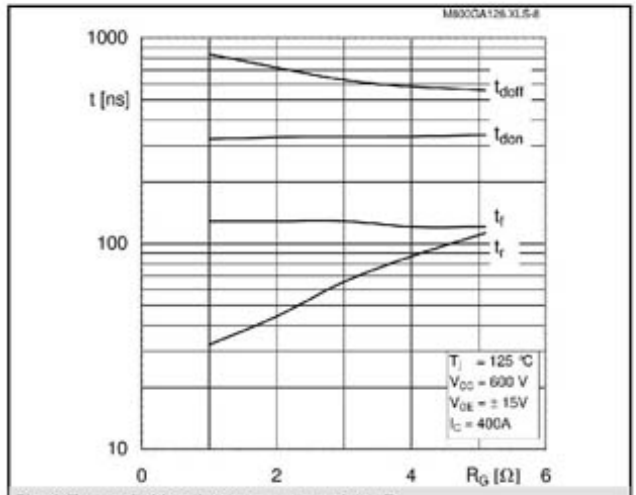


Fig. 8 Typ. switching times vs. gate resistor R_G

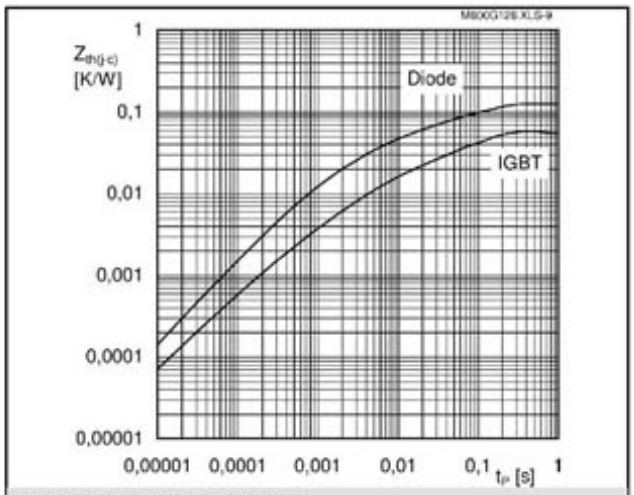


Fig. 9 Transient thermal impedance

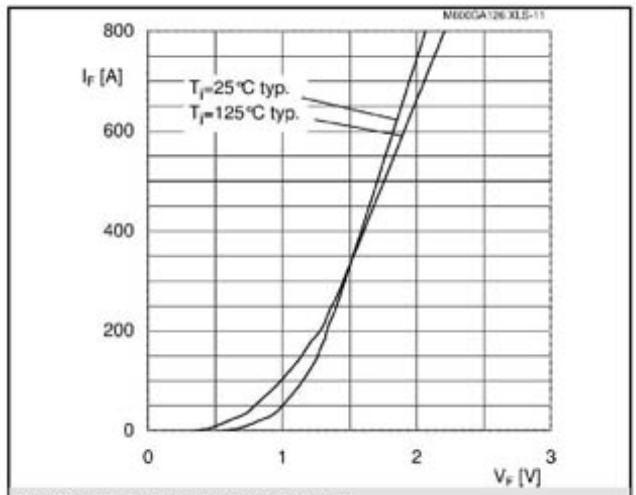


Fig. 10 CAL diode forward characteristic

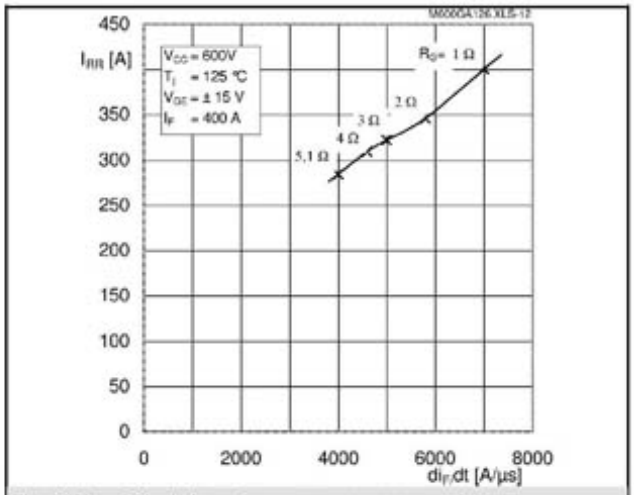


Fig. 11 Typ. CAL diode peak reverse recovery current

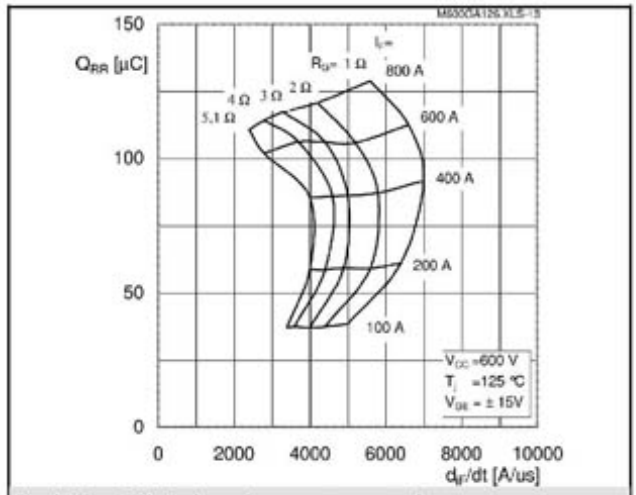
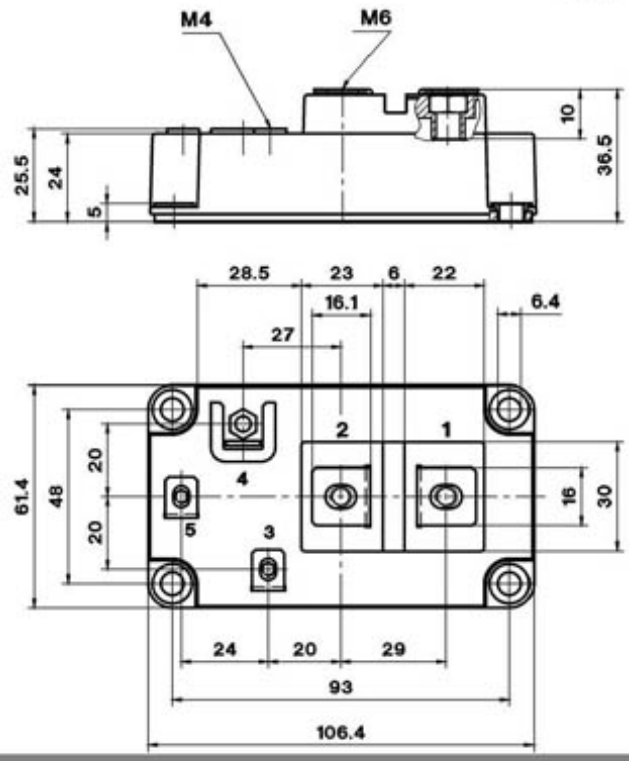


Fig. 12 Typ. CAL diode peak reverse recovery charge

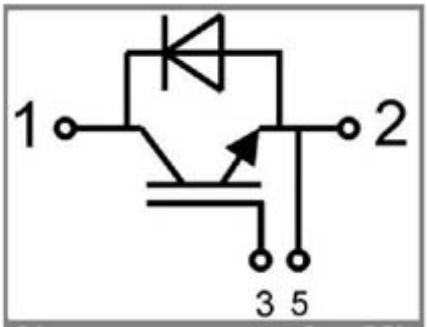
UL Recognized

File no. 63532

CASED59



Case D 59



GA Case D59

